U.S. Department of Commerce, Patent and Trademark Office						Docket N	0.	Serial No.			
						2200-ID U	JS	Unassigned 10/658			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT						Applicant(s)					
(Use several sheets if necessary)						Chia-Shun Hsiao					
						g Date		Group Unassigned			
						with					
			U.S. I	Patent Documents							
1 1		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate			
A.M	AA	5,940,717	17 Aug. 1999	Rengarajan et al.							
	AB	6,127,215	3 Oct. 2000	Joachim et al							
	AC	6,130,129	10 Oct. 2000	Chen							
	AD	6,200,856 B1	13 Mar. 2001	Chen							
	AE	6,319,794 B1	20 Nov. 2001	Akatsu et al.							
	AF	6,355,524	12 Mar. 2002	Tuan et al.							
	AG	6,518,618	11 Feb. 2003	Fazio et al.							
	АН										
	AI										
	AJ										
	AK										
			Foreign	Patent Documents							
								Tran	slation		
		Document	Date	Country		Class	Subclass	Yes	No		
	AL										
	AM										
/	AN										
		OTHER	ART (Including A	uthor, Title, Date, Po	ertinent	Pages, E	tc.)				
A.M	AO	Aritome, S. et al. "A 0.67um ² Self-Aligned Shallow Trench Isolation Cell (SA-STI Cell For 3V-only 256Mbit NAND EEPROMs," International Electron Devices meeting 1994, San Francisco, CA December 11-14, 1994, pages 94-61 – 94-64.									
	AP	Keeney, Stephen N., "A 130nm Generation High Density Etox TM Flash Memory Technology, Intel, Corporation, Santa Clara, CA USA 42 Sheets.									
	AQ	Silicon, Flash and Other Non-Volatile Memory Technologies, http://www.inttel.com/research/silicon/flash.htm , September 12, 2002, pages 1-4.									
	AR	Comprising A F	ield Dielectric Etc	No. 10/262,785, entitl h With A Horizontal et No.: M-12841 US	Etch C						
xaminer ^	NH >		Date Considere		,						
EXAMINER		f reference conside	ered, whether or no	ot citation is in confo opy of this form with	rmance						

U.S. Department of Commerce, Patent and Trademark Office Atty Docket No. Serial No. M-12200-1D US 10/658,934 INFORMATION DISCLOSURE STATEMENT BY APPLICANT Applicant(s) (Use several sheets if necessary) Chia-Shun Hsiao Filing Date Group JAN 1 3 2004 September 9, 2003 Unassigned U.S. Patent Documents *Examiner Elah Document Filing Date Initial Number Date Name Class Subclass If Appropriate 6,376,877 23 Apr 2002 Yu et al. AA A.M 10 Sept. 2002 AΒ 6,448,606 Yu et al. 6,417,047 AC 9 July 2002 Isobe AD ΑE AF AG ΑH ΑI ΑJ ΑK Foreign Patent Documents Translation Document Class Subclass Yes Date Country No ALAM AN OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) AO AP AQ AR ANH 16 Examiner MAi Date Considered *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

1 3 2004	벙						She	et
D.S. Departm	of Cor	mmerce, Patent and	Atty Docket	Serial No. 10/658,934				
A LINE Y	<u> </u>		M-12200-1D					
- NOT OR	MATION	DISCLOSURE ST	TATEMENT BY	APPLICANT	Applicant(s)			
		(Use several sheets	if necessary)		Chia-Shun H	siao		
		·····		Filing Date	Group			
					September 9	, 2003	Unassigned	
			U.S. 1	Patent Documents				
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing I	
A.M	AA	6,649,472	Nov. 2003	Hsieh, Chia-Ta				
	AB	6,228,713	May 2001	Pradeep et al.				
	AC	6,323,085	Nov. 2001	Sandhu et al.				
	AD	6,222,225	24 Apr. 2001	Nakamura et al.				
	AE							
	AF							
• /	AG							
	AH							
	AI							
/	AJ							
/	AK							
			Foreign	Patent Documents				
		Y	т —	_	,	T	Tran	ısl
		Document	Date	Country	Class	Subclass	Yes	\perp
A.M	AL	JP-2000-174242	June 2000	Japan				1
	AM		ļ					1
	AN					<u></u>		1
		OTHER A	ART (Including A	uthor, Title, Date, P	ertinent Pages,	Etc.)		
/	AO							
	AP							
	AQ							
/	AR							